

ABSTRACT

[Abstract]

[Means for Solving]

A semiconductor device 10 comprises a P type base region 13 formed in an N⁻ type base region 11, and N⁺ type emitter regions 14 formed plurally in the P type base region 13 so as to be spaced from each other. The N⁺ type emitter regions 14 are formed such that the rate of the area occupied by the N⁺ type emitter region 14 in the P type base region 13 at the center part of the semiconductor device 10 is smaller than the rate of the area occupied by the N⁺ type emitter region 14 in the P type base region 13 at the peripheral part of the semiconductor device 10.

[Selected Drawing]

FIG. 1